

[EASI - 5376.wsp.1]

File View Edit Tools Window Help

Active

- ☒ L2: (6259) ((implanting implantation implant\$2 diffus\$3) with (gas\$2)) with (void porous pore mi...)
- ☒ L3: (200) 2 and transistor
- ☒ L4: (172) 3 and (source drain)
- ☒ L5: (385) 4 (channel adj region) with (void porous pore micro adj por\$3 cavity cavities buble)
- ☒ L6: (385) 4 ((channel adj region) with (void porous pore micro adj por\$3 cavity cavities buble))
- ☒ L7: (0) 4 and ((channel adj region) with (void porous pore micro adj por\$3 cavity cavities buble))
- ☒ L8: (3) 4 and (channel adj region)
- ☒ L9: (1) 1 and ((implanting implantation implant\$2 diffus\$3) with (channel))
- ☒ L10: (49704) (channel) with (void porous pore micro adj por\$3 cavity cavities buble)
- ☒ L11: (213) (channel adj region) with (void porous pore micro adj por\$3 cavity cavities buble)
- ☒ L12: (124) 11 and (implanting implantation implant\$2 diffus\$3)
- ☒ L13: (8) 12 and ((implanting implantation implant\$2 diffus\$3) with (gases gas))
- ☒ L14: (1) "6046098".PN.
- ☒ L15: (1) "5924001".PN.

Failed

- ☒ (0) 47 and (implanting implantation implant\$2) with (void))
- ☒ (0) ((implanting implantation implant\$2 diffus\$3) with (gas\$2)) wirh (void porous pore micro ad...
- ☒ (0) ((implanting implantation implant\$2 diffus\$3) with (gas\$2)) with (void porous pore micro ad...

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20030145726	20030807	10	Use of an adsorbent in solid foam form for the purification or separation	95/96	95/90;
	A1							96/121;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20020074598	20020620	12	Methodology for control of short channel effects in MOS transistors	257/345	257/349;
	A1							257/E21-335;
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20020020053	20020221	35	Deposited thin films and their use in	29/623.1	156/249;

Details

Ready

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2 L8: (3) 4 and (channel adj region)
 2 L9: (1) 1 and ((implanting implantation implant\$2 diffus\$3) with (channel))
 2 L10: (49704) (channel) with (void porous pore micro adj por\$3 cavity cavities buble)
 2 L11: (213) (channel adj region) with (void porous pore micro adj por\$3 cavity cavities buble)
 2 L12: (124) 11 and (implanting implantation implant\$2 diffus\$3)
 2 L13: (3) 12 and ((implanting implantation implant\$2 diffus\$3) with (gases gas))
 2 L14: (1) "6046098".PN.

12 and ((impla...)

All hit terms initially

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20030145726 A1	20030807	10	Use of an adsorbent in solid foam form for the purification or separation	95/96	95/90; 96/121;	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20020074598 A1	20020620	12	Methodology for control of short channel effects in MOS transistors	257/345	257/349; 257/E21.335;	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20020020053 A1	20020221	35	Deposited thin films and their use in separation and sacrificial layer applica	29/623.1	156/249; 204/192.12;	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6362082 B1	20020326	13	Methodology for control of short channel effects in MOS transistors	438/523	257/E21.335; 257/E21.339;	
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6281532 B1	20010828	13	Technique to obtain increased channel mobilities in NMOS transisto	257/288	257/418; 257/E21.195;	
6	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6228694 B1	20010508	14	Method of increasing the mobility of MOS transistors by use of localized s	438/199	257/E21.618; 257/E21.619;	
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4651184 A	19870317	12	Dram cell and array	257/302	257/E27.096	
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20020074598 A	20020620		Method for reducing short-channel effects in MOS transistor involves im			

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